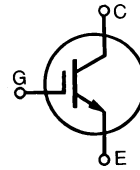


Preliminary data

HiPerFAST™ IGBT

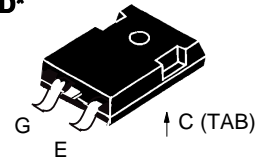
IXGH22N50B IXGH22N50BS

$$\begin{aligned} V_{CES} &= 500 \text{ V} \\ I_{C(25)} &= 44 \text{ A} \\ V_{CE(sat)typ} &= 2.1 \text{ V} \\ t_{fi(typ)} &= 55 \text{ ns} \end{aligned}$$

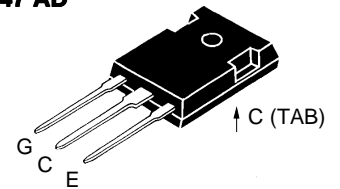


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	44	A
I_{C90}	$T_C = 90^\circ\text{C}$	22	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	88	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 44 \text{ A}$ @ $0.8 V_{CES}$	
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		TO-247 AD	6 g
		TO-247 SMD	4 g

TO-247 SMD*



TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages
JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High frequency IGBT
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on
- drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

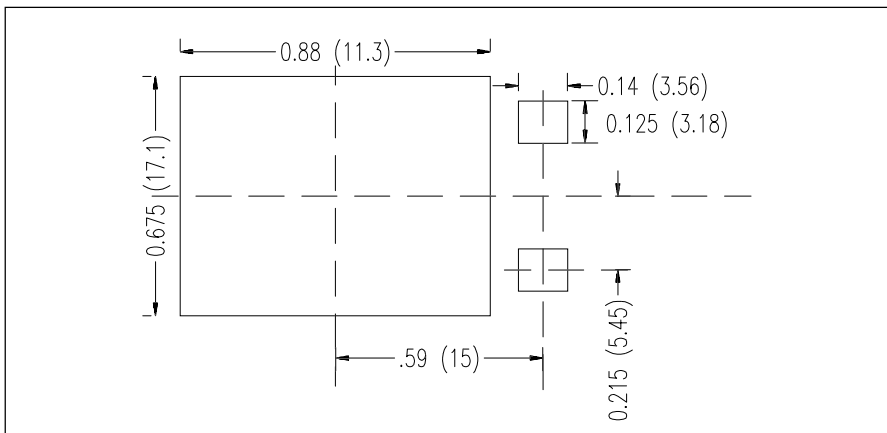
- High power density
- Very low switching losses for high frequency applications
- Easy to mount with 1 screw, TO-247 (insulated mounting screw hole)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	500		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	200 μA 1 mA
I_{OES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$		± 100	nA
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	2.1	2.5	V

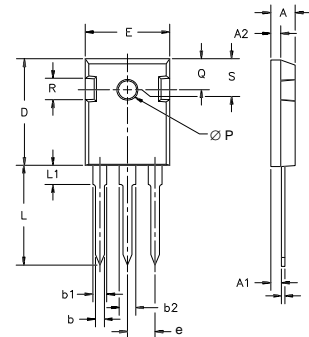
Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	9	16	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	120	1450	pF
C_{oes}			37	pF
C_{res}	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		90	nC
Q_{ge}			11	nC
Q_{gc}			30	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$, $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 10\ \Omega$ Note 1		15	ns
t_{r}			30	ns
E_{on}			0.15	mJ
$t_{d(off)}$			100	ns
t_{f}			55	ns
E_{off}			0.3	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 100\ \mu\text{H}$, $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 10\ \Omega$ Note 1		15	ns
t_{r}			30	ns
E_{on}			0.15	mJ
$t_{d(off)}$			140	ns
t_{f}			100	ns
E_{off}			0.6	mJ
R_{thJC}				0.83 K/W
R_{thCK}		0.25		K/W

Note 1: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G

Min. Recommended Footprint (Dimensions in inches and mm)

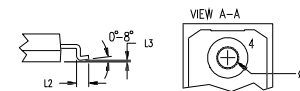
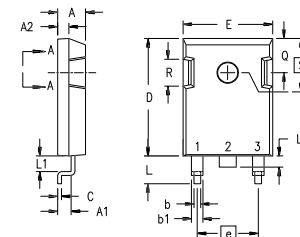


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-247 SMD Outline



- Gate
- Collector
- Emitter
- Collector

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	4.90	5.10	.193	.201
L ₁	2.70	2.90	.106	.114
L ₂	2.10	2.30	.083	.091
L ₃	0.00	0.10	.00	.004
L ₄	1.90	2.10	.075	.083
ØP	3.55	3.65	.140	.144
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	6.15	BSC	.242	BSC

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025